

Customer No.: 31561  
Application No.: 10/064,882  
Docket NO.: 7857-US-PA

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**IN THE SPECIFICATION**

Please amend the following text paragraphs as follows.

[0026] To program the flash memory cell, a portion of the gate structure 124 and the source region 112 can be regarded as an equivalent source region ~~112~~ 112'. Hence, size of the drain region is much smaller than the equivalent source region ~~112~~ 112'.

During the programming operation, the equivalent channel length  $L_{eq}$  is also much shorter than the original channel length  $L$ . Therefore, hot electrons will exit the channel somewhere along the gate structure 120 to be subsequently trapped inside the nitride layer 120b after passing through the oxide layer 120a (Fig. 3).

[0027] Since the hot electrons inject into the nitride layer halfway through the channel (the side of equivalent source region ~~112~~ 112') rather than from the original source region 112, trajectories of the hot electrons are little affected by the original electron distribution in the source region 112. In other words, source-side injection and second bit effect are prevented using a flash memory cell with this hexagonal gate structure.